

■ Productor Character

- Half Bridge Rectified、Common Cathode Structure.
- Multilayer Metal -Silicon Potential Structure.
- Beautiful High Temperature Character.
- Have Over Voltage protect loop, high reliability.
- RoHs Product.

■ Primary Use

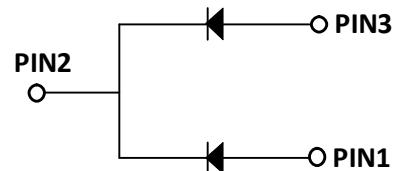
- Low Voltage High Frequency Switching Power Supply.
- Low Voltage High Frequency Invers Circuit.
- Low Voltage Continued Circuit and Protection Circuit.

■ Summarize

- MBR10150CT/MBR10150FCT Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications.

Device Weight :

ITO-220AB-1.48g TO-220AB-1.96g TO-263-1.78g



Absolute Maximum Ratings

Item	Symbol	Data	Unit
Maximal Inverted Repetitive Peak Voltage	VRRM	150	V
*Average Rectified Forward Current (Rated VR-20Khz Square Wave) - 50% duty cycle	IFAV	10	A
Typical Thermal Resistance (per leq Package =TO-220AB/TO-263 Package =ITO-220AB)	$R_{\theta JC}$	2	$^{\circ}\text{C}/\text{W}$
		4	$^{\circ}\text{C}/\text{W}$
Forward Peak Surge Current(Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	IFSM	150	A
Maximum Rate of Voltage Change (at Rated VR)	dv/dt	10000	V/uS
Peak Repetitive Reverse Surge Current (2uS-1Khz)	IRRM	0.5	A
Operating Junction Temperature	TJ	-40- +175	$^{\circ}\text{C}$
Storage Temperature	TSTG	-40- +175	$^{\circ}\text{C}$

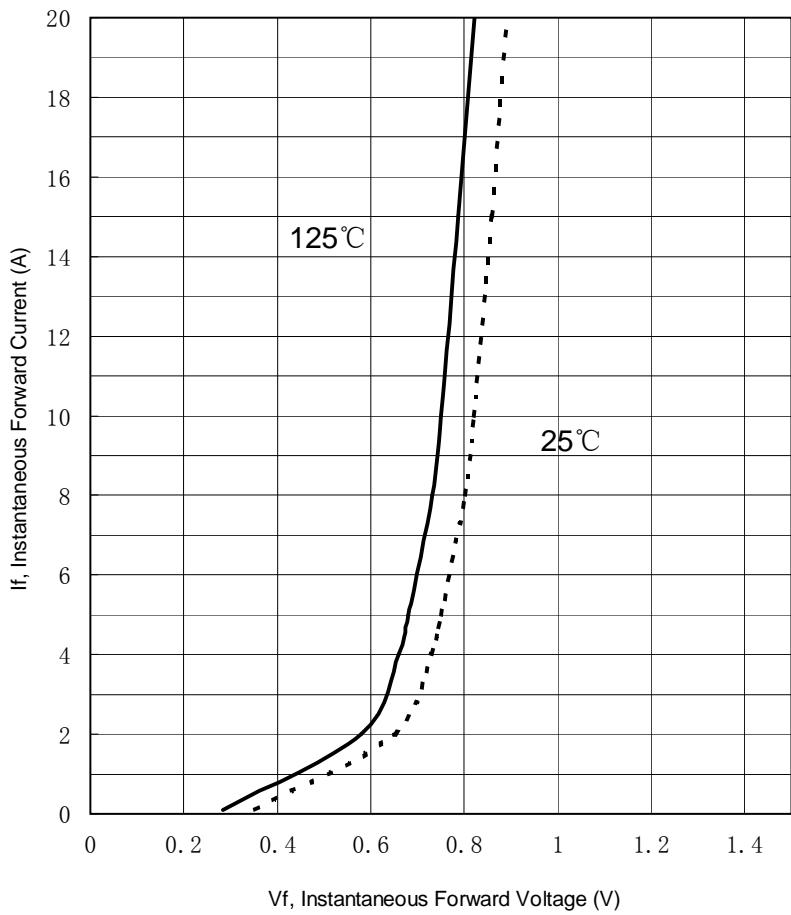
Electricity Character

Item	Test Condition		TYP.	MAX.	Unit
IR	TJ =25°C	VR=VRRM		10	uA
	TJ =125°C			1	mA
VF	TJ =25°C	IF=5A	0.85	0.88	V
	TJ =125°C	IF=5A		0.79	V

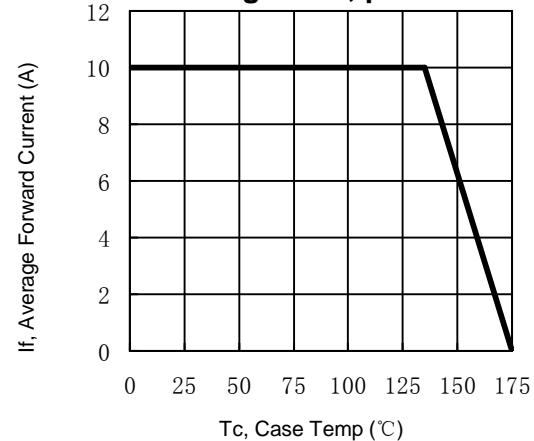
*IF(AV)= 5A×2

Characteristic Curves

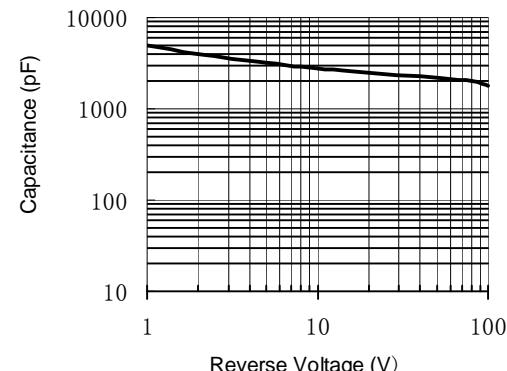
The forward voltage and forward current curve



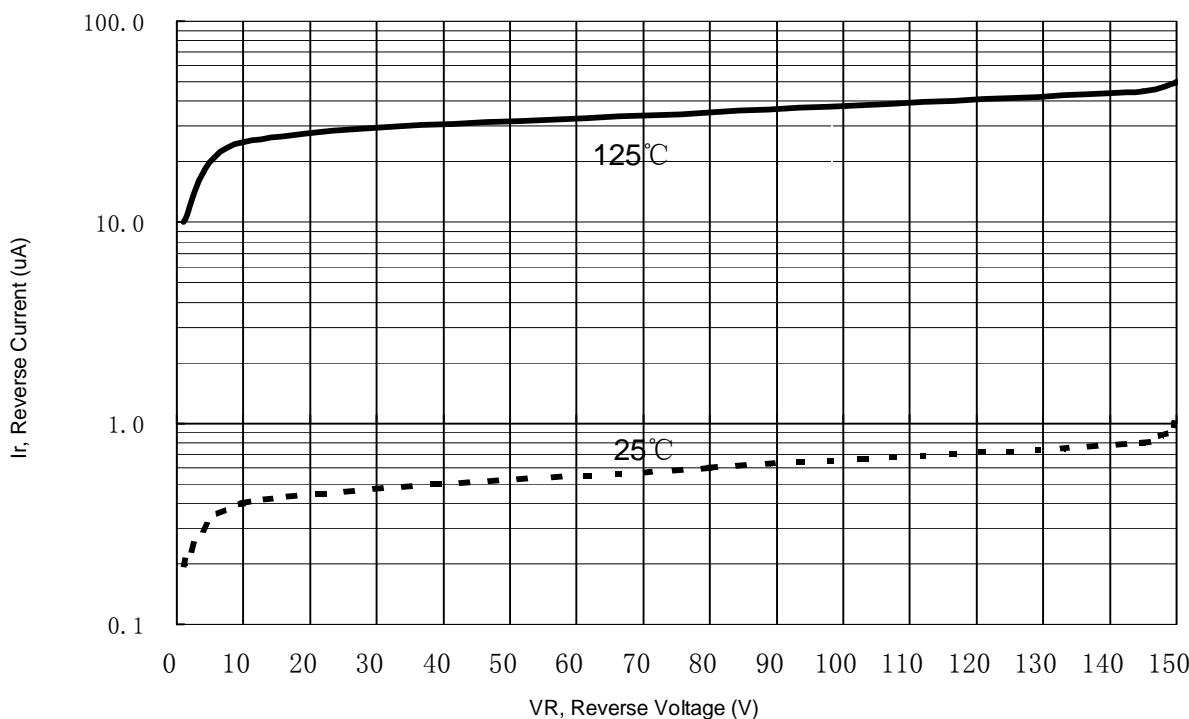
Current derating curve, per element



The crunode capacitance curve

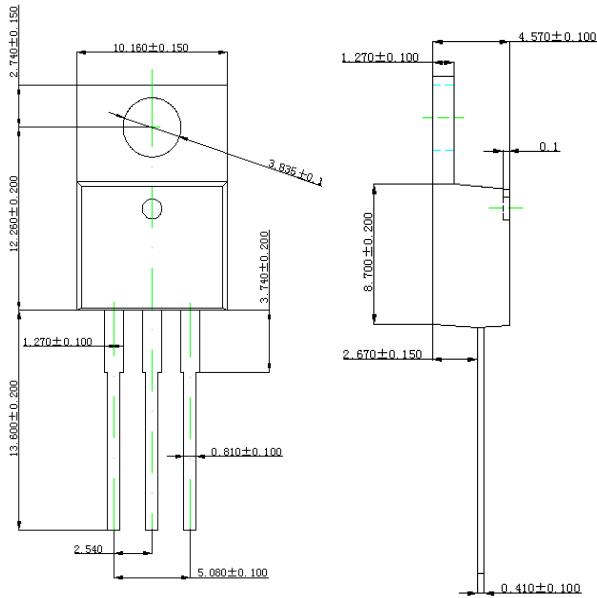


The reverse leak current and the reverse voltage (single-device) curve.

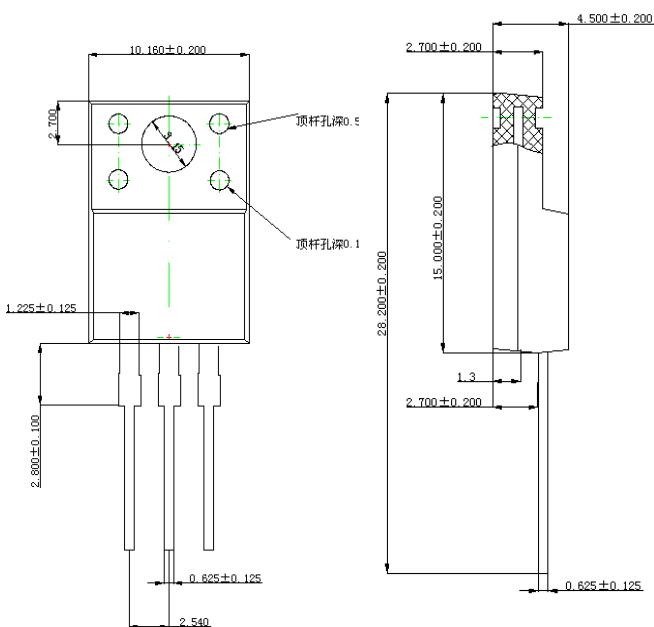


Package Outline Dimensions

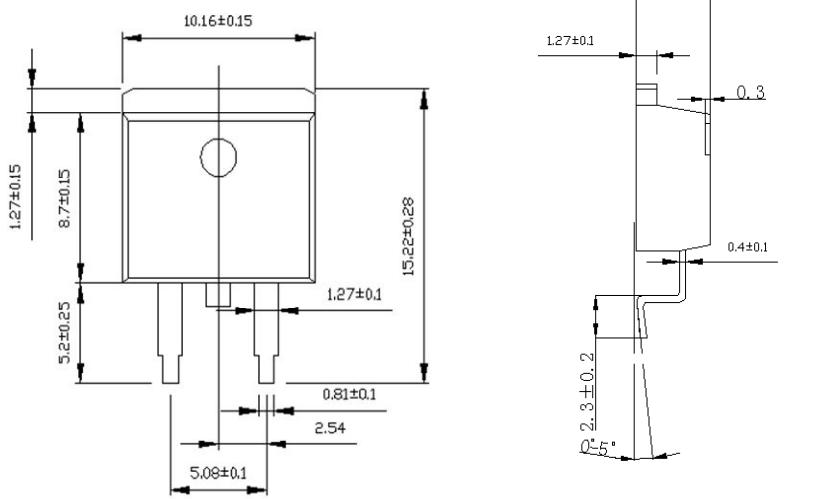
TO-220



ITO-220

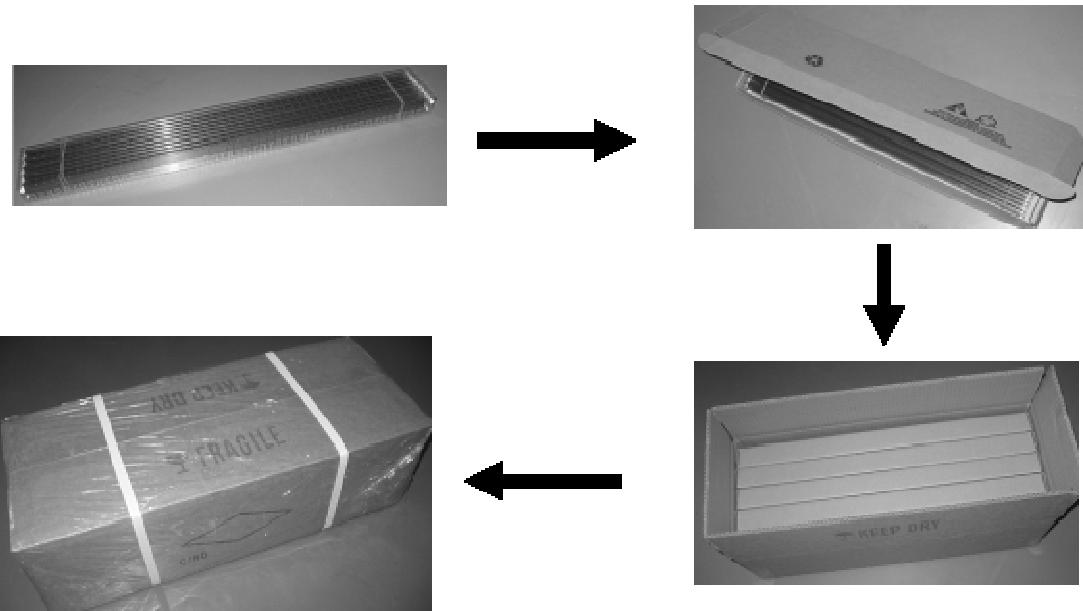


TO-263



Packing Information

Part Number	Package	Delivery Mode
MBR10150CT	TO-220/TO-263	50 pieces / tube
MBR10150FCT	ITO-220	50 pieces / tube



Part Number	Quantity	Size (mm)
tube	50 pieces	530*33*7
inner box	1000 pieces	560*150*40
outer container	5000 pieces	580*230*170

Marking

1. ASEMI 为 LOGO。
2. MBR10150CT 为产品型号。
3. XXXX 代表日期码，第一码表示公元年的最后一码，第二码表示生产时当月码 (A,B,C…为一月, 二月, 三月…), 第三, 四码表示大量生产时批次码
例如: 2013年第一月生产的, D/C为3AXX。
4. ITO-220 封装后面加“F”区别



High-Voltage Schottky Diodes

MBR10150CT/MBR10150FCT

Label

内盒标签（尺寸：125*32mm）格式：

PART NO.: XXXXXX



RoHS

DATE: 20140526 DE27



Q'TY: 1000 PCS



PART NO: 产品型号；

DATE CODE: 产品周号；

QTY: 实物数量；

例如：XXXXXXXX/3J43/1000/20130615001016

例如

外箱标签（尺寸：75*64mm）格式：



RoHS

PART NO.: XXXXXX



DATE: 20140526 DE27



Q'TY: 5000 PCS



PART NO: 产品型号；

DATE: 产品包装日期；

QTY: 产品数量。

注意事项

- 1) 凡本公司出厂的产品，均符合相应规格书的电参数和外形尺寸要求；对于客户有特殊要求的产品，双方应签订相关技术协议。
- 2) 在安装时，要注意减少机械应力的产生，安装扭矩推荐值0.3牛/米，防止由此引起的产品失效。
- 3) 避免靠近发热元件；焊接上锡时要注意控制温度和时间，焊接温度小于260°C，10S。
- 4) 产品储存需注温度与湿度的控制，一般情况下，温度在5°C-25°C，湿度50%条件下，可存放一年，过保存期后，使用前需重新测试。
- 5) 静电及高压会对产品产生损坏，使用和检验产品时，佩戴防静电腕带或手套，设备工具可靠接地。